Assessing the performance of Mg₂Si and Ca₂Si from DFT and SLME calculations for solar cell applications

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The present work investigates the performance parameters of low-cost & nontoxic Mg₂Si and Ca₂Si compounds for photovoltaic (PV) applications by using density functional theory (DFT) and spectroscopic limited maximum efficiency (SLME) calculations. For this purpose, a detailed analysis of electronic and optical properties has been performed by using PBE, PBEsol and mBJ exchange-correlation functionals. The band-gap for Mg₂Si (Ca₂Si) is found to be in the range of 0.25-0.6 (0.57-0.96) eV with an indirect (a direct) in nature. Moreover, the density of state effective mass at top of the valence and bottom of the conduction band is obtained to be in the range of 0.14-0.17 (1.17-1.25)m_e and 0.27-0.29 (0.3-0.41)m_e, respectively. The real and imaginary parts of the dielectric function show a sharp maximum of magnitude ~40 (15.6) at ~2.6 (0.7) eV and ~47 (14) at ~2.7 (2.6) eV, respectively. Further, the highest absorption coefficient in the solar spectrum active region is found to be ~1.45 (0.8) ×10⁶ cm⁻¹. The SLME with respect to the depletion width (W₀) of an ideal single-junctional solar cell is estimated. The highest SLME at 300 K is obtained to be ~3.89 (31.21)%. The required concentrations of acceptor and donor atoms to achieve this SLME are ~10¹⁸ cm⁻³ and ~0.45 (0.12) ×10¹⁶ cm⁻³, respectively, which corresponds to a W₀ of ~0.42 (0.84) μm . The present study suggests that Ca₂Si (Mg₂Si) is a potential candidate for single-junction (bottom cell in multi-junction) thin-film solar devices.

I. INTRODUCTION

Semiconductors are playing a significant role in the current technological revolution. The light-matter interaction in semiconductors is an interesting topic in modern research as well as in industrial applications [1]. One of the most significant technologies for the generation of renewable energy is PV solar cells. For example, one common question when making solar cells is how much of the incident sunlight is able to be absorbed through the optically active materials and how these materials might be adjusted to absorb more light and generate a large number of electron-hole (e-h) pairs. It also becomes critical to understand how one can optimize the materials that efficiently convert these e-h pairs into useful electricity. Therefore, the analysis of optical properties gives starting idea regarding the above aspects.

Efficient solar devices do not always rely on optical parameters [2]; they also depend on the type of bandgap as well as the solar cell parameters such as shortcircuit current density (J_{sc}) , open-circuit voltage (V_{oc}) , and fill-factor (FF), etc. [2–4]. Some successful theoretical studies using the first principles approach have identified new solar materials with high power conversion efficiency (PCE) for PV applications [2, 5, 6]. One of the famous theoretical calculations to predict the maximum efficiency of a single-junctional solar cell is SLME, in which Yu et al. [2] introduce the SLME from the Shockley-Queisser (SQ)-limiting efficiency [7]. The information on band-gap, absorption spectra, and recombination characteristics is required for SLME. But additional investigations are required to examine several other factors that may affect the efficiency such as effective mass of charge carriers, dopant concentrations, dielectric constant, and costs of materials, *etc.* [8]. From the design perspective of a thin-film solar device, a reasonable size of thickness should be used, which is greatly affected by one of the extrinsic factors called the doping concentration of donor and acceptor atoms in a compound [8, 9].

The current worldwide scenario is that more than 80% of installed PV systems are first-generation solar cells, which are manufactured from mono- or multicrystalline silicon-based materials [10] with a typical thickness of about $0.2 \ nm$. Their production is still expensive, although extremely efficient. Therefore, in order to expand the use of PV cells quickly, a reduction in manufacturing costs while maintaining good efficiency is essential. Likewise, to reduce these costs, a transition from crystalline silicon solar cells to thin-film or second generation technologies must be required [11]. After years of research, various thin-film solar materials, including CdTe, GaAs, CIGS, and InP, have been developed successfully in the lab with efficiencies of 22.1%, 29.1%, 23.4%, and 24.2%, respectively [12, 13]. But these non-silicon compounds still face major drawbacks related to toxicity (Cd, Te, As), low abundance (Ga, In), and long-term device stability in ambient conditions, which prevent their widespread implementation. For this reason, silicon is the foundation for designing thin-film solar cells [8, 14–16].

The current work includes much attention to the choice of PV solar elements that are environmentally friendly, low-cost, earth-abundant, and non-toxic in nature. One of the most interesting categories of silicon-

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based materials is semiconducting silicides [17, 18], which may be used in thin-film solar technology due to their high absorption coefficient [19, 20]. Mg₂Si semiconductor [18] shows an excellent optoelectronic properties such as suitable and appropriate experimental band-gaps in the range of 0.65-0.80 eV [21-24] and a large absorption coefficient from reflectance measurements of almost $3 \times 10^5 \ cm^{-1}$ at visible energy of 2.5 eV [21, 25]. These unique features may make it a perfect solar absorber material. Another various experiments have been performed for Mg_2Si , including Raman scattering [26], reflectivity spectra [27], infrared reflectivity spectroscopy [28], electro-reflectance measurements [29], X-ray diffraction [30], and photo-emission spectroscopy [31], to calculate the physical properties and related quantities. The empirical pseudopotential method predicted an indirect band-gap of Mg_2Si with a value of 0.53 eV [32]. Another empirical pseudopotential calculation was given a band-gap value of 0.49 eV [33]. The *ab-initio* pseudopotential method also predicted an indirect gap of 0.118 eV [34]. According to first principles pseudopotential study of Imai et al., an indirect gap value is 0.28 eV [35]. Neither these theoretical gaps are close to experimental gaps nor consistent with each other. Hence, one motivation is clear- to calculate a comparable band gap with experiments for Mg_2Si , which has great dependence on the exchange and correlation (XC) potentials used in DFT calculations. Au et al. have attempted the empirical pseudopotential method for the calculation of dielectric function [32]. On the other hand, dielectric function was also estimated from the all electron PAW method with e-h excitation effects for Mg₂Si [36]. But this calculation demands a large computational effort. As is known, the optical parameters are very sensitive to the band gap. Therefore, after benchmarking a proper XC term, which gives the band gap closer to the experiment gap, comparable optical properties can be obtained at a reasonable computational cost. After that, cubic Ca₂Si compound is chosen for studying the electronic and optical properties, which is experimentally less studied. The reason for selecting is to have a suitable DFT direct band gap of 0.56 eV for PV cells [37]. The study by Lebèque et al. [38] reported a band-gap from DFT and GW approximation (GWA) of 0.56 eV and 1.16 eV, respectively. The same study also reported the dielectric function from the quasipartical correction (with and without local field) upon DFT. One may rely on the selection of the XC potential, which is already benchmarked for Mg_2Si , to determine the optoelectronic properties of Ca₂Si. Another motivation is that these two interesting silicides are never explored in the context of determining the PCE by analyzing the complete solar cell parameters such as J_{sc} , V_{oc} , FF, and *etc.* These parameters are obtained by writing a Python code, which will be thoroughly discussed later.

Therefore, the present paper is focused on a detailed first-principles study by using of three exchange and correlation potentials (PBE, PBEsol and mBJ) to estimate the solar cell properties for Mg₂Si and Ca₂Si, with an aim of optimizing their SLME. The predicted band-gaps from mBJ for Mg₂Si and Ca₂Si are $\sim 0.60 \text{ eV}$ and ~ 0.96 eV, respectively. The density of state effective mass at high-symmetric points is also estimated. Further, the maximum value of static dielectric constant for Mg_2Si (Ca₂Si), which is an important quantity to calculate W_0 , is estimated to be almost 18 (13.7). Both silicides show a large absorbance (order of 10^6 cm^{-1}) in an active area of the solar spectrum. But higher absorption can't guarantee an efficient single-junctional solar cell; therefore, the SLME for an ideal pn-junction solar cell with respect to W_0 is estimated. A maximum possible SLME at 300 K for Ca₂Si and Mg₂Si is predicted to be $\sim 31.21\%$ and $\sim 3.89\%$, respectively. One can get the calculated SLME at a concentration of $\sim 10^{18} \ cm^{-3}$ acceptor and $\sim 0.12 \ (0.45) \ \times 10^{16} \ cm^{-3}$ donor atoms in Ca₂Si (Mg₂Si). A W_0 of ~0.84 μm is obtained from these dopant atoms for Ca₂Si, which can be used to make thin-film single-junctional solar cell. Finally, a narrowgap Mg₂Si with high absorption coefficient can be a suitable material for fabricating a bottom layer in multijunctional solar devices.

II. COMPUTATIONAL DETAILS

Electronic structure and optical properties calculations were performed by using of full-potential linearized augmented plane wave (FP-LAPW) method within DFT as implemented in WIEN2k [39] code. The muffin-tin sphere radii (R_{MT}) value was kept fixed to 2.5 Bohr for all atoms. Also, a 10×10×10 k-mesh size and convergance criteria of 10⁻⁴ Ry/cell for total energy were taken to solve the Kohn-Sham (KS) equation. Further two different functionals, *i.e.*, PBE [40] and PBEsol [41] were considered as a XC part of the KS equation.

The dielectric function was calculated from the random-phase approximation [42] by only taking the inter-band contribution of the KS orbitals. The polarizability, which is required for calculating the dielectric function, was estimated at the independent particle approximation level. Meanwhile, the **k**-mesh was built into a large 5000 k-points over the full Brillouin zone to obtain the momentum matrix elements. The Lorentzian broadening value of 0.15 eV was used. The "scissor correction" was also applied at PBE band-gap to get better description of optical parameters. The components of an effective mass tensor using the degenerate perturbation approach were obtained by the mstar code implemented in WIEN2k software [43]. Effective mass calculation in this framework is very sensitive to the momentum matrix elements that contain upper energy bands. Thus, these matrix elements were obtained within the maximum energy of 10 Ry, which corresponds to the 236 and 164 bands for Ca₂Si and Mg₂Si, respectively. The tolerance parameter of degeneracy energy was used as 10^{-5} Ha.

III. RESULTS AND DISCUSSION

A. Electronic properties

Here, the electronic and optical properties of Mg₂Si and Ca₂Si compounds have been investigated in their anti-fluorite structure with a space group of Fm $\bar{3}$ m (No. 225). The used value of lattice parameters in the entire calculations for Mg₂Si and Ca₂Si is 6.35 Å, and 7.16 Å, respectively. The value of lattice parameter for Mg₂Si is very close to the experimental value [44]. The primitive unit cell of both compounds consists of three atoms, in which one Si atom is located at the (0, 0, 0) and two Mg(Ca) atoms are situated at the position of (0.25, 0.25, 0.25) and (0.75, 0.75, 0.75). All these above structural parameters are directly taken from the AFLOW database [45].

Calculation of band gap from electronic dispersion offers a promising way to find appropriate PV materials. Optical processes have been related to vertical (or direct) transitions. The number of photo-excited electrons in conduction bands (CB) strongly depend on the band gap, thus an accurate description of the band gap is essential for materials used in solar cell technology. The $\epsilon_2(\omega)$ in Eq. (1) is also directly related to the eigenvalues of occupied and unoccupied states. The DFT band structure gives accurate information regarding the shape of energy bands, but a major problem with this theory is that it generally underestimates the band-gap of semiconductors or insulators. This is because it does not properly treat the XC potential, such as the self-interactions error in GGA or LDA and the lack of density-functional derivative discontinuity in the XC energy [46]. To handle the exchange potential in a proper way, the mBJ potential [47] has been taken into account here to get the best possible band gaps of compounds because the accuracy of this method has been proven by the experimental results [48].

Therefore, the electronic dispersions for both silicides have been calculated from PBE & PBEsol functional, and mBJ potential, which are presented in Fig. 1. It is noticed that the band gap increases in the silicides by replacing the light Mg atom with a heavy Ca atom. In Fig. 1(a), Mg_2Si is found to be an indirect band-gap semiconductor, which has the location of valence band maxima (VBM) and conduction band minima (CBM) at the Γ - and X-point, respectively. The band gap from PBE (PBEsol) is found to be ~ 0.25 (0.16) eV, while the gap from mBJ is calculated to be ~ 0.6 eV. These gaps are almost 62-69 (75-80)% smaller, whereas have best match as compared to the gap obtained from several experimental measurements, respectively [21–24]. The minimum direct band-gap (optical gap) has been located at the Γ -point. The estimated value of an optical-gap from PBE (PBEsol) is ~ 1.9 (1.76) eV, while it is ~ 2.45 eV from mBJ. These gaps underestimates the experimental value by almost 12 (19)%, but overestimates it by almost 13% from respective methods [21]. Next, from Fig.



FIG. 1: Electronic band dispersion for (a) Mg₂Si, (b) Ca₂Si along the high-symmetric directions.

TABLE I: The band-gaps in eV obtained from PBE/PBEsol functional and mBJ potential and compared with the available experimental band-gap.

Methods	Mg_2Si	Ca_2Si
PBE functional	0.25	0.57
PBEsol functional	0.16	0.52
mBJ potential	0.60	0.96
Experimental	0.65 [21], 0.78 [23], 0.80 [24], 0.77 [22]	-

2(a), Ca₂Si is a direct band-gap semiconductor with a value of ~0.57 (0.52) eV at a X-point obtained from the PBE (PBEsol) method, and the calculated gap from the mBJ potential is ~0.96 eV. Unfortunately, experimental band-gap is not available for cubic Ca₂Si. The last valence band (VB) near Fermi energy (E_F) seems to be less (more) dispersive in the direction of Γ -L (Γ -X) and X- Γ (X-W) for Mg₂Si and Ca₂Si, respectively. These behaviors of bands in the respective directions are crucial for understanding the optical properties of both studied silicides.

The transition of electrons from filled to empty bands is critical to the interaction of light with semiconductors. As in Eq. (1), the success of such transitions depends on the number of available states as well as the transition probability of electrons from occupied to unoccupied states at a particular photon energy. Thus, in Fig. 2, the total density of states (TDOS) along with the partial density of states (PDOS) plots have been shown. Both compounds show a band gap near the E_F , which is a nature of being semiconducting compounds. For Mg₂Si,



FIG. 2: Total/partial density of states (T/PDOS) plots for Mg₂Si and Ca₂Si.

one can notice the sharp rise in states at the topmost (bottom-most) region of the VB (CB), which is a good sign for solar materials. The PBE states have not seen too many changes in the inclusion of mBJ potential. Two maximum peaks in the VB region are located around the energies of ~ -1.95 and ~ -4.17 eV. In the CB region, the largest peak is found around the energy of ~ 2.7 eV. Similarly, in Fig. 2(b) of Ca_2Si , there have been sharply increasing states in the vicinity of the E_F on the VB side. These VB states are shifted by $\sim 0.2 \text{ eV}$ on the lower energy side by adding mBJ in PBE, while states in CB have not changed significantly. The maximal peaks in the VB and CB regions from PBE (mBJ) are situated at nearly -0.35 (0.6) eV and ~ 2.3 eV, respectively. The PDOS obtained from mBJ has been shown, in which the electronic states of VB are significantly contributed by the Si-3p orbital. In Fig. 2(c), the gap is mainly coming from the Si-3p and Si-3s orbitals in the VB and CB regions. Similarly, in Fig. 1(d), the whole VB and CB regions are rich in Si-3p character with a low contribution from Ca-4s,4p states. The Si-3p and Ca-3p states in the VB and CB regions, respectively, have been responsible for creating the band gap and may also be actively involved in the photo-conversion process.

The effective mass of the charge carriers (electrons and holes) in the vicinities of CBM and VBM is of great importance for analyzing the carrier transport mechanisms such as charge mobilities and then current density in the PV materials [43, 49]. The density of states effective mass (m_{dos}^*) of these charge carriers directly affect the electrical conductivity [50], and depletion width of the pn-junction solar cells based on intrinsic concentration [8, 49, 51]. Therefore, in Table-II, the m_{dos}^* is calculated at high-symmetric points for the last filled VB and first empty CB in the vicinity of E_F . The m_{dos}^* is obtained from the geometric mean of the principal components of the effective mass tensor (m_1^*, m_2^*, m_3^*) , *i.e.*, $\sqrt[3]{m_1^* \times m_2^* \times m_3^*}$ [43]. The m_{dos}^* in VBM is observed to be almost 0.14-0.17m_e and 1.17-1.25m_e, whereas in CBM, it is ~ 0.27 - $0.29m_e$ and ~ 0.30 - $0.41m_e$ for Mg₂Si and Ca_2Si , respectively. The estimated m_{dos}^* of electron for Mg₂Si at CBM is well matched with previously available theoretical effective mass (m^*_{\perp}) of $0.25m_e$ [52]. The negative (positive) value of m_{dos}^* at VB (CB) corresponds to a hole (electron) effective mass [53]. The experimental effective masses obtained from Morris et al. [23] are $0.47m_e$ (for electron) and $0.87m_e$ (for hole), while those from Heller et al. [24] are $0.5m_e$ (for electron) and $2.0m_e$ (for hole). In another study, Udono et al. [54] found effective masses of $0.57m_e$ (for electron) and $1.07m_e$ (for hole), while Nolas et al. [55] found $0.51m_e$ (for electron). In Table-II, the m_{dos}^* of *p*-type carriers in VB is larger than that of n-type carriers (similar trend as observed in experiment), and this is because the slop of DOS below E_F exceeds that above. One possible reason for the difference between the calculated and experimental m_{dos}^* would be that the calculated m_{dos}^* is k-points dependent, whereas the reported experimental results provides the

TABLE II: Calculated density of states effective mass m^*_{dos} (units of free electron mass (m_e)) at high-symmetric points for the VB and the CB extrema of Mg₂Si and Ca₂Si.

	Values of m [*] _{dos} for Mg ₂ Si/Ca ₂ Si compound							
High-	PBE fur	ictional	mBJ potential					
symmetric points	VB	CB	VB	CB				
W	0.28/0.70	0.79/0.60	0.30/1.19	0.77/0.57				
L	0.51/0.64	0.22/0.65	0.56/0.91	0.24/0.66				
Г	0.14/0.50	0.13/0.20	0.17/0.80	0.16/0.64				
Х	-0.47/1.17	0.27/0.30	-0.50/1.25	0.29/0.41				
К	-0.64/8.80	0.39/0.45	-0.69/-6.54	0.41/0.51				
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overall value for the materials. However, the values in Table-II are in the range of experimental values. For an excellent PV materials, the effective mass should be low, which corresponds to high mobility of electrons/holes at the CB/VB and resultantly high conductivity. For any material, it is reported that excellent carrier mobility can be obtained by having an effective mass value lower than $0.5m_e$ in at least one direction [56, 57]. In Table-II, at least one high-symmetric point has a m_{dos}^* value of less than $0.5m_e$; therefore, both compounds may have great charge mobilities in the vicinities of VBM and CBM.

B. Optical properties

The operation and efficiency of any solar device are greatly affected by the optical properties of the underlying compound. Basically, these properties are obtained from the response function calculations in terms of frequency and wavevector dependent complex dielectric function $\epsilon(\omega)$. The $\epsilon(\omega)$ has two contributions, which are due to inter-band and intra-band transitions. The contribution by the intra-band transitions is only significant for metals. The inter-band transitions are further classified as direct and indirect transitions. Here, the indirect inter-band transitions, which involve phonon scattering and are expected to contribute not much to $\epsilon(\omega)$ [58], are ignored. To obtain the contribution of direct inter-band transitions to the imaginary part of the dielectric function $\epsilon_2(\omega)$, one should take summation over all possible electronic transitions from filled to empty states.

$$\epsilon_{2}(\omega) = \frac{Ve^{2}}{2\pi\hbar\omega^{2}m^{2}}\sum_{nm}\int \mathrm{d}^{3}\mathbf{k} \mid < n\mathbf{k} \mid \mathbf{p} \mid m\mathbf{k} > \mid^{2} f(n\mathbf{k}) \times [1 - f(m\mathbf{k})]\delta(E_{n\mathbf{k}} - E_{m\mathbf{k}} - \hbar\omega),$$
(1)

Where $\hbar\omega$ is the incident photon energy, **p** is related to the momentum operator $(-\iota\hbar\partial/\partial x)$, $|n\mathbf{k}\rangle$ is the eigenfunction with energy eigenvalue of $E_{n\mathbf{k}}$, and $f(n\mathbf{k})$ indicates the Fermi-distribution function. The δ function confirms that the energy is conserved in the photoconversion process. The estimation of matrix elements of momentum operator is performed separately over the muffin-tin and the interstitial regions. A complete description of the evaluation of these matrix elements can be found in the paper of *Draxl et al.* [42].

The real part of dielectric function $\epsilon_1(\omega)$ can be obtained from the Kramers-Kronig relation [42, 59] as:

$$\epsilon_1(\omega) = 1 + \frac{2}{\pi} \int_0^\infty \frac{\epsilon_2(\omega')\omega'd\omega'}{\omega'^2 - \omega^2} \tag{2}$$

For a good accuracy of $\epsilon_1(\omega)$ calculation, one needs to take good representation of $\epsilon_2(\omega)$ up to high energies. In the present study, $\epsilon_2(\omega)$ is calculated up to 100 eV and also this value used as a truncation energy in Eq. (2). Finally, the other optical parameters such as refractive index, absorption coefficient, and reflectivity can be easily obtained [42, 59].

It is important to note that the thermoelectric transport properties can be explained in better way by considering the band-gap correction on the different XC functionals [60–62]. Since both thermoelectric and PV transport properties are highly dependent upon electronic band structures, it would not be worthless at all to consider a scissor value for analyzing the PV properties. This value for Mg₂Si and Ca₂Si is used to be 0.35 eV and 0.39 eV, respectively, which is the difference between the band-gap energy of mBJ and PBE calculations.

The calculated $\epsilon_1(\omega)$ and $\epsilon_2(\omega)$ for both silicides are presented in Fig. 3. In both materials, the static value of the real part of the dielectric function $\epsilon_1(0)$ decreases as the gap increases. This could be explained by the strong relationship between the electronic and optical properties via the dielectric constant. The polarization tells about the interaction strength between the electronic states of the VB and the CB in the presence of an external electric field. The corresponding interaction is limited for the large band gap materials and consequently gives a small polarization and hence a small dielectric constant [63]. Thus, Ca_2Si has comparatively lower values of $\epsilon_1(\omega)$ than the Mg₂Si compound. The maximum $\epsilon_1(0)$ for Mg₂Si is found to be almost 18 (from PBE), while this value for Ca₂Si is estimated to be almost 13.7. The scissor correction is not too effective in Mg_2Si , but it has significant changes in $\epsilon_1(\omega)$ result for Ca₂Si as compared to the mBJ calculation. The highest peak of $\epsilon_1(\omega)$ for both silicides is obtained in the visible energy region (from mBJ), which is a good feature regarding PV technology. The frequency at which the $\epsilon_1(\omega)$ turns from a positive to a negative region corresponds to the plasma frequency [64].

In Fig. 3(c), the calculated $\epsilon_2(\omega)$ spectra and a comparison of the experimental result [32] for Mg₂Si are presented. The value of $\epsilon_2(\omega)$ is observed to be very low in an infrared part of the photon energy. As seen from the figure, the values from PBEsc and mBJ of $\epsilon_2(\omega)$ are best matching the experiment in the visible energy region up to almost 2.6 eV. The calculated spectra follow almost the same trend as observed in the experiment. The only bright peak obtained is situated at ~2.71 eV (from PBE), which is closer to the energy of the highest experimental peak of ~2.73 eV. But these peaks are



FIG. 3: The calculated real $\epsilon_1(\omega)$ and imaginary $\epsilon_2(\omega)$ part of dielectric function. In sub-figure (c), the experimental data [32] of $\epsilon_2(\omega)$ for Mg₂Si is plotted for comparison.



FIG. 4: The calculated real $n(\omega)$ and imaginary $k(\omega)$ part of refractive index for both Mg₂Si and Ca₂Si compounds.

different magnitude-wise, in that the calculated spectra have a magnitude of almost 47 (from PBE), far from the experimental value of almost 68. A tiny hump is also observed at energies of ~3.67 eV (from mBJ) and ~3.75 eV (from the experiment). A possible reason for the deviation from the experimental data may be due to not considering the e-h interaction and local field effects. The computed $\epsilon_2(\omega)$ for Ca₂Si is presented in Fig. 3(d). Until now, experimental data on the optical properties of Ca₂Si have not been available. In this silicide, the energy region of almost 1.7 eV to ~4 eV can strongly participate in the photo-conversion process. Finally, due to the strong feature of $\epsilon_2(\omega)$ in the visible energy region, both silicides may fall into the category of the best PV materials.

The information of complex refractive index is crucial in designing the anti-reflection coating surface and accurately predicting the optical behavior of real solar devices. The obtained curves of the real part $(n(\omega))$ as well as the imaginary part $(k(\omega))$ of the refractive index are presented in Fig. 4. As seen from Figs. 4(a)&(b), the $n(\omega)$ follows the same trend as observed in the $\epsilon_1(\omega)$ plot of respective compounds. The range of n(0) is observed to be almost 4.0–4.26 for Mg₂Si and almost 3.1-3.7 for the Ca₂Si. The $n(\omega)$ in both silicides gets the strongest part in the infrared and visible energy range, which means that photons are absorbed very fast in this region. The value of highest $n(\omega)$ in Mg₂Si and Ca₂Si



FIG. 5: The calculated absorption coefficient $\alpha(\omega)$ and reflectivity $r(\omega)$ for Mg₂Si and Ca₂Si. The experimental data in (a) and in (c) are from the reference [25] and [21], respectively.

is predicted to be almost 6.65 (from mBJ) and 4 (from PBE), respectively. Next, the extinction coefficient $k(\omega)$ gives information on light absorption within the studied energy regime. In both silicides, the $k(\omega)$ shows almost rapid increasing behavior in the almost whole visible energy region. The range of maximum intensity of $k(\omega)$ for Mg₂Si and Ca₂Si is found to be ~2.6-4.0 eV and ~2.4-4.0 eV, respectively, which means photons within this range have more importance in the creation of *e*-*h* pairs.

The absorption coefficient $\alpha(\omega)$ and reflectivity $r(\omega)$ are two important parameters that determine the performance of materials to be used in the application of PV devices. The obtained $\alpha(\omega)$ and $r(\omega)$ are illustrated in Fig. 5. Both curves of $\alpha(\omega)$ in Figs. 5(a)&(b) show almost linear behavior with photon energy in the visible light. The obtained $\alpha(\omega)$ in Fig. 5(a) is completely unmatched with experimental data, except for the experimental absorption edge at ~ 2.6 eV [25]. This discrepancy may arise from the indirect band-gap nature of Mg₂Si, since optical calculation only considers direct transitions. Ca₂Si has a large absorbance than Mg₂Si in the visible energy part of $\sim 1.65 - 2.65$ eV (from PBEsc), while in the remaining visible part ($\sim 2.65 - 3.27 \text{ eV}$) viceversa behavior is observed. The highest intense peak in the visible energy regime is found to be at $\sim 1.45 \times 10^6$ cm^{-1} and $\sim 0.8 \times 10^6$ cm^{-1} for Mg₂Si and Ca₂Si, respectively. The $r(\omega)$ for Ca₂Si in visible region is found to be in the range of $\sim 0.31 - 0.38$ (from PBEsc), while it is $\sim 0.41 - 0.61$ for Mg₂Si. The calculated spectra of Mg₂Si follow an almost similar trend with the experiment [21] up to an energy of almost 2.6 eV. After this energy, our estimated $r(\omega)$ is not too much closer to the experimental value.

The obtained optical properties for Mg₂Si are much more comparable with silicon, whereas these properties for Ca₂Si have the best match with various solar compounds such as InAs, GaAs, and GaP [65]. Thus, both silicides may be used in PV solar cells. But the type of band gap has a major impact on the selection of an efficient solar devices [2]. It should also be noted that the calculation of optical properties only considers vertical transition between filled and empty states. Therefore, we have to move on to the next section to check the importance of the band-gap type on the performance of solar cell devices.

C. SLME analysis

To understand the factors used for designing a solar device, it is important to briefly review the theory behind efficient solar cells. It is well known that, the performance of solar devices is characterized by their PCE, which is used here as SLME. This SLME is calculated as the ratio of the maximum output power density (P_{max}) to the total incoming solar power density (P_{in}) [2],

$$SLME = \frac{P_{max}}{P_{in}} \tag{3}$$

The P_{max} is estimated by taking the numerically maximum product of total current density (J) and voltage (V) over the absorber layer. Furthermore J of an illuminating solar cell under photon flux (I_{sun}) at temperature T under ideal diode condition, is obtained as;

$$J = J_{sc} - J_0(e^{eV/k_BT} - 1)$$
(4)

The first term is short-circuit current density, while second term is known as the reverse saturation current. $J_0 = J_0^r + J_0^{nr} = J_0^r/f_r$ corresponds to the total (radiative J_0^r plus nonradiative J_0^{nr}) *e-h* recombination current at equilibrium in the dark, and f_r is the fraction of the radiative recombination current, approximated in SLME by $e^{-\Delta/k_BT}$ [2]. The $\Delta = E_g^{da} - E_g$, where E_g^{da} and E_g are the direct-allowed and minimum band-gap of a material, respectively. Further, J_{sc} is defined as;

$$J_{sc} = e \int_0^\infty a(E) I_{sun}(E) dE$$
(5)

Where e is the elementary charge and I_{sun} is the standard AM1.5G flat-plate solar spectrum at 25 °C[66]. The a(E) stands for the photon absorptivity $(1 - e^{-2\alpha(E)L})$, where $\alpha(E)$ is material absorption coefficient and L is the thickness of thin-film material with zero and unityreflectivity from the front and back surface, respectively.

According to the concept of detailed balance [7], in equilibrium conditions, the rate of emission of photons via radiative recombination must be equal to an absorption of photons through the cell surface from the surrounding medium in dark. Because a cell is surrounded by an ideal heat sink, and surrounding temperature is to be considered same as a solar cell. Hence, the rate of absorption of black-body photons at temperature T by the front cell surface from the surrounding thermal bath gives J_0^r and

$$J_0^r = e\pi \int_0^\infty a(E) I_{bb}(E,T) dE$$
(6)

TABLE III: The estimated solar cell parameters such as width of depletion region (W₀), built-in potential across *pn*-junction (V_b), open-circuit voltage (V_{oc}), *fill-factor* (FF), SLME, and Shockley-Queisser (SQ) limit based on density of states effective mass for valence $(m_{v,dos}^*)$ and conduction $(m_{c,dos}^*)$ band, doping concentration of acceptor (N_a) and donor (N_d) atoms, relative permittivity (ϵ_r) of both compounds at 300 K using PBE, PBE with scissor correction (PBEsc), and mBJ methods.

Materials	methods	$m_{v,dos}^{*}$	$m^*_{c,dos}$	$N_a(cm^{-3})$	$N_d(cm^{-3})$	ϵ_r	$W_0(\mu m)$	$V_b(V)$	$V_{oc}(\mathbf{V})$	FF	SLME(%)	SQ limit(%)
Ca ₂ Si	PBE	$1.17 \mathrm{m}_e$	$0.3 \mathrm{m}_e$	10^{18}	0.32×10^{16}	13.7	0.30	0.31	0.38	0.76	17.94	17.88
	PBEsc	$1.17 m_e$	$0.3 m_e$	10^{18}	0.12×10^{16}	11.6	0.84	0.66	0.73	0.85	31.21	31.24
	mBJ	$1.25 m_e$	$0.41 \mathrm{m}_e$	10^{18}	$0.46{ imes}10^{15}$	9.7	1.2	0.62	0.73	0.85	31.21	31.24
Mg ₂ Si	PBE	$0.14m_e$	$0.27 \mathrm{m}_e$	10^{18}	0.68×10^{20}	18	0.012	0.32	0.01	0.28	0.033	3.13
	PBEsc	$0.14m_e$	$0.27 m_e$	10^{18}	0.45×10^{16}	16.4	0.42	0.43	0.31	0.73	3.89	19.37
	mBJ	$0.17 \mathrm{m}_e$	$0.29 \mathrm{m}_e$	10^{18}	$4.7{\times}10^{15}$	16.4	0.40	0.42	0.32	0.73	3.89	19.37

where $I_{bb}(E,T)$ is the black-body radiance. Finally, the SLME from Eq. (3) is abtained as;

$$SLME = \frac{\max[J \times V]_V}{\int_0^\infty EI_{sun}(E)dE}$$
(7)

In addition to SLME, we also address V_{oc} , FF, built-in potential (V_b) across pn junction, and width of the depletion region (W_0) . V_{oc} is a voltage of a pn junction solar cell when value of J become zero in Eq. (4),

$$V_{oc} = \frac{k_B T}{e} \ln\left(\frac{J_{sc}}{J_0} + 1\right) \tag{8}$$

The FF, which is a figure of merit for a PV cell, is defined as the $P_{max}/J_{sc}V_{oc}$ [8]. To derive the maximum SLME, we shall consider the thickness of a solar cell equal to W₀ which is the condition to become an ideal cell and defined as [8],

$$W_0 = \left[\frac{2\epsilon(N_a + N_d)V_b}{eN_aN_d}\right]^{1/2} \tag{9}$$

Where $\epsilon = \epsilon_0 \epsilon_r$. $N_a(N_d)$ is the acceptor(donor) carrier concentration in a solar cell material. Finally, V_b is defined as the $(k_B T/e) \ln(N_a N_d/n_i^2)$, where n_i is the carrier concentration [49] and written as,

$$n_i(T) = \frac{1}{4} \left(\frac{2k_B T}{\pi \hbar^2}\right)^{3/2} (m_{v,dos}^* m_{c,dos}^*)^{3/4} e^{-E_g/2k_B T}$$
(10)

Where $m_{v,dos}^*$ and $m_{c,dos}^*$ are the density of states effective mass of VB and CB, respectively. Therefore, from Eq. (9), N_a and N_d are most critical parameters to define the thickness of a solar material and then SLME.

We now have all the desired information for estimating the SLME after calculating the band-gap, dielectric constant, density of states effective mass, and absorption coefficient of both silicides. As per our assumption, W_0 should be equal to material thickness Lfor ideal solar cells; therefore, analysis of W_0 is much needed before going to solve Eq. (4). Now from Eq. (9), one can get different values of W_0 with different values of



FIG. 6: Current density J and power density P of absorbing layer at a thickness W₀ of (a) $\sim 0.30 \ \mu m$ from PBE and $\sim 1.2 \ \mu m$ from mBJ for Ca₂Si (b) $\sim 0.40 \ \mu m$ from mBJ for Mg₂Si, with respect to the voltage at 300 K.



FIG. 7: SLME for (a) Ca₂Si and (b) Mg₂Si compound with respect to the thin-film thickness at 300 K.

the doping parameters N_a and N_d for a given material. After that, we must have a maximum output power at a specific value of W₀. Therefore, one can determine the SLME from Eq. (7) with knowledge of N_a and N_d parameters. Now, the maximum SLME is obtained for specific sets of N_a and N_d for both silicides, which are shown in Table-III. The maximum SLME is obtained as almost 31.21% and ~3.89% for Ca₂Si and Mg₂Si, respectively.

In order to make a deep analysis of SLME, we first analyze the current-voltage (J-V) and power-voltage (P-V) plots in Fig. 6 at a particular W₀, which has maximum SLME for both silicides. All the calculations have been done at room temperature (300 K). In Fig. 6 (a), the area under the P-V curve seems to be larger for mBJ than PBE, which is the main reason for the so-great difference in the SLME. The maximum output power P for Ca₂Si is estimated to be ~312 Wm^{-2} . Consequently, FF is calculated to be almost 0.85, which is a good value used in solar cell. Due to the indirect band-gap nature of Mg₂Si, the obtained properties in Table-III are significantly lower than the Ca₂Si results. In Fig. 6(b), J_{sc} value is obtained to be almost 170 Am^{-2} , with an estimated V_{oc} of ~0.32 V. This lower value produces a less amount of output power, which is almost 39 Wm^{-2} .

Based on the above studied solar parameters for both silicides, the SLME with respect to absorbing layer thickness is calculated and is presented in Fig. 7. At higher thicknesses, the obtained SLME for Ca₂Si returns to the corresponding SQ-limit, since for a thick absorbing layer, the absorptivity becomes a step function. In Table-III, the SLME ($\sim 17.94\%$) exceeds the SQ value $({\sim}17.88\%)$ at W_0 of ${\sim}0.3~\mu m$ for Ca₂Si. One possible explanation for this behavior may be how J_{sc} and J_0 are used to obtain P_{max} from Eq. (7), because f_r is one. The value of J in Fig. 6(a) remains the same as J_{sc} up to a certain voltage, and thus, J_0 plays a role in deciding the P_{max} . The J_0 value, which depends upon the material's a(E) via Eq. (6), increases as the band gap is lowered. Therefore, Ca₂Si (from PBE) is more likely to have a large P_{max} than the SQ- P_{max} , and consequently, a high SLME than SQ-efficiency. Finally, the highest SLME ($\sim 3.89\%$) for Mg₂Si is much lower than the SQlimit ($\sim 19.37\%$). This is because of indirect band-gap, which gives a large difference between E_g^{da} and E_g (Δ = E_q^{da} - $E_q = \sim 1.85 \text{ eV}$), and hence f_r is the order of 10^{-22} . This fraction is used to calculate J_0 , which makes J_0 to a unreasonably large. This means that the nonradiative e-h recombination is dominating here, which results in a substantially smaller overlap between the absorption spectrum and the solar spectrum. In such a scenario, a high value of J_0 produces a V_{oc} that is too little to create any substantial power density. Therefore, although the $\alpha(\omega)$ near direct-gap is much stronger (~2.3×10⁶ cm⁻¹) in Mg_2Si , but the SLME is still small.

The SLME only differs from the SQ-limit by introducing an *ab initio* obtained absorption spectrum; thus, results indicate that the SQ-limit is not a theoretical upper limit under an assumptions of a detailed balance technique. The above calculated carrier doping and W_0 are only valid for an ideal *pn*-junction solar cells. But the knowledge of many other internal parameters of materials, such as recombination lifetimes as well as the mobilities of electrons and holes, is essential to get a more close picture from an ideal to a real or practical PV device [8]. The highest SLME ($\sim 31.21\%$) for Ca₂Si can be achieved at a thin-film thickness of almost 0.84 μm , which is obtained at a doping concentration of almost $10^{18} \ cm^{-3}$ acceptor and $\sim 0.12 \times 10^{16} \ cm^{-3}$ donor atoms. This SLME value is found to be larger as compared to various silicon superlattices [67] and several silicon-based crystals [5]. The significantly lower SLME obtained for Mg₂Si makes it a less efficient single-junctional solar compound, but one may use for bottom cell to absorb the lower-energy part of the solar spectrum in multi-junctional PV modules.

IV. CONCLUSIONS

In the present work, the solar parameters of cheap, eco-friendly, and earth-abundant Mg₂Si and Ca₂Si materials are investigated using DFT and SLME approaches. In this direction, the electronic structure and dependent optical properties are studied using three XC-functionals, viz., PBE, PBEsol and mBJ. The calculated indirect and direct band-gaps are in the range of 0.25-0.6 eV and 0.57-0.96 eV for Mg₂Si and Ca₂Si, respectively. The m_d^* of electrons and holes at high-symmetric points for band extrema is also obtained. The $\epsilon_1(\omega)$ ($\epsilon_2(\omega)$) contains a sharp peak around 2.6 (2.7) eV and 0.7 (2.6) eV with values of ~ 40 (47) and ~ 15.6 (14) for Mg₂Si and Ca₂Si, respectively. In addition to this, the maximum $\alpha(\omega)$ in an active area of the solar spectrum is found to be $\sim 1.45 \times 10^6 \ cm^{-1}$ and $\sim 0.8 \times 10^6 \ cm^{-1}$, respectively. The SLME of an ideal pn-junction solar device with respect to W_0 from the *J*-*V* plot is also investigated. For Ca₂Si, the highest SLME at 300 K is \sim 31.21% at a W₀= \sim 0.84 μm for $\sim 10^{18} \ cm^{-3}$ acceptor and $\sim 0.12 \times 10^{16} \ cm^{-3}$ donor atoms. The maximum predicted SLME for Mg₂Si at 300 K is almost 3.89% at a W₀ of ~0.42 μm for ~10¹⁸ cm^{-3} acceptor and $\sim 0.45 \times 10^{16} \ cm^{-3}$ donor atoms. Therefore, the above results can be more helpful for experimental community to design solar devices from these silicides.

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